

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN MMS-MMY/14/8745 Dated 21 Oct 2014

RX95HF, Design improvement for die version rationalization

Table 1. Change Implementation Schedule

,	
Forecasted implementation date for change	14-Oct-2014
Forecasted availability date of samples for customer	14-Oct-2014
Forecasted date for STMicroelectronics change Qualification Plan results availability	14-Oct-2014
Estimated date of changed product first shipment	20-Jan-2015

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	RX95HF-VMD5T
Type of change	Product design change
Reason for change	Die version rationalization
Description of the change	Design improvement inducing IDN response change from FS2JAST3 to FS2JAST4
Change Product Identification	Marking changed to RX95HFV5 LE
Manufacturing Location(s)	

Table 3. List of Attachments

Customer Part numbers list	
Qualification Plan results	

	>\$
Customer Acknowledgement of Receipt	PCN MMS-MMY/14/8745
Please sign and return to STMicroelectronics Sales Office	Dated 21 Oct 2014
Qualification Plan Denied	Name:
Qualification Plan Approved	Title:
	Company:
🗖 Change Denied	Date:
Change Approved	Signature:
Remark	

Name	Function
Fidelis, Sylvain	Marketing Manager
Rodrigues, Benoit	Product Manager
Pavano, Rita	Q.A. Manager

DOCUMENT APPROVAL



PRODUCT / PROCESS CHANGE NOTIFICATION

RX95HF,

Design improvement for die version rationalization

What is the change?

The **RX95HF**, NFC Receiver IC, assembled in VFQFPN32 and processed with the CMOSF9 process technology at ST Rousset (France) 8" wafer diffusion plant, has underwent a **design improvement** for **die version rationalization**.

Following parameter will be updated in revised datasheet rev. 10, October 2014:

- Customer information

 Response to IDN command (ASCII): FS2JAST4 (ROM code Rev 4) (was FS2JAST3 for ROM code Rev 3)

Why?

The strategy of STMicroelectronics Memory Division is to support our customers on a long-term basis. In line with this commitment, the qualification of the RX95HF with the new design will improve the production capacity throughput and consequently improve the service to our customers.

When?

The production of the new version of the RX95HF will ramp up from October 2014 and shipments can start from January 2015 onward (or earlier upon customer approval).

How will the change be qualified?

The new RX95HF will be qualified using the standard ST Microelectronics Corporate Procedures for Quality & Reliability.

The Qualification Report QRMMY1231 rev. 2 is available and included inside this document.

What is the impact of the change?

- Form: Marking change (see Device marking paragraph)
- Fit: No change
- Function:
 - IDN command response changed

How can the change be seen?

- BOX LABEL MARKING

The difference is visible inside the **Finished Good Part Number** where the mask revision identifier is "**E**" for the **new design**, this identifier being "A" for the current version.

nics	Manufactured under patents or patents pending Country Of Origin: XXXX Pb-free 2 nd Level Interconnect MSL: 1 NOT MOISTURE SENSITIVE	
0	PBT: 260 °C Category: e4 ECOPACK2/ROHS	
cth	TYPE: RX95HF-VMD5T RX95HF-VMD5T L B E	
le	Total Qty: 3000 Process Technology Mask revision: Assembly and Test & Finishing plants "E" for new design	
oe	"A" for previous version	1
CL	Marking RX95HFV5	
STMicroelectronics	Bulk ID X0X00XXX0000 IIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIIII	

-

How can the change be seen? <u>- DEVICE MARKING</u>

The difference is visible inside the product name:

- New design is RX95HFV5, current design being RX95Y5 Also, the additional marking is "LE" for new design, current one being "L"

New design

Current



RX95HF, Design improvement for die version rationalization

Appendix A- Product Change Information

Product family / Commercial products:	RX95HF-VMD5T
Customer(s):	All
Type of change:	Design change
Reason for the change:	Die version rationalization
Description of the change:	Design improvement inducing IDN response change from FS2JAST3 to FS2JAST4
Forecast date of the change: (Notification to customer)	Week 42 / 2014
Forecast date of	
Qualification samples availability for	
customer(s):	Available
Forecast date for the internal	
STMicroelectronics change,	The Qualification Report QRMMY1231 rev. 2
Qualification Report availability:	is available and included inside this document.
Marking to identify the changed product:	RX95HFV5 LE
Description of the qualification program:	Standard ST Microelectronics Corporate Procedures for Quality and Reliability
Product Line(s) and/or Part Number(s):	RX95HF-VMD5T
Manufacturing location:	Rousset 8 inch wafer fab
Estimated date of first shipment:	Week 03 / 2015

RX95HF, Design improvement for die version rationalization

Appendix B: Qualification Report:

See following pages



QRMMY1231 Qualification report

New product / RX95HF using the CMOSF9 technology in the Rousset 8" Fab

General information			
Commercial product	RX95HF-VMD5T		
Product description	Near field communication transceiver for tag emulation		
Product group	MMS		
Product division	MMY - Memory		
Silicon process technology	CMOSF9		
Wafer fabrication location	RS8F - ST Rousset 8 inch, France		
Electrical Wafer Sort test plant location	ST Rousset, France		

Table 1. Product information

Table 2. Package description

Package description Qualified assembly plant location		Qualified final test plant location
32-lead VFQFPN (5 x 5 mm)	Subcontractor Amkor, Philippines	Subcontractor Amkor, Philippines

Reliability / Qualification assessment: PASS

1 Reliability evaluation overview

1.1 Objectives

This qualification report summarizes the results of the reliability trials that were performed to qualify the new product RX95HF using the CMOSF9 silicon process technology in the ST Rousset 8" diffusion fab.

The voltage and temperature range covered by this document are:

• 2.7 to 5.5V at -25°C to +85°C

The CMOSF9 silicon process technology is already qualified in the ST Rousset 8" diffusion fab and in production for MMS products.

This document serves for the qualification of the named product, using the named silicon process technology in the named diffusion fab.

1.2 Conclusion

The new product RX95HF using the CMOSF9 silicon process technology in the ST Rousset 8" diffusion fab has passed the reliability requirements and the product described in *Table 1* is qualified.

Refer to Section 3: Reliability test results for details on the reliability test results.



2 Device characteristics

The RX95HF is an integrated transceiver IC for contactless applications. The RX95HF embeds an Analog Front End to provide the 13.56 MHz Air Interface. The RX95HF supports ISO/IEC 14443 Type A communication in Tag Emulation mode. Refer to the product datasheet for more details.



3 Reliability test results

This section contains a general description of the reliability evaluation strategy.

The named products are qualified using the standard STMicroelectronics corporate procedures for quality and reliability.

The product vehicle used for the qualification is presented in Table 3.

Product	Silicon process technology	Wafer fabrication location	Package description	Assembly plant location
RX95HF	CMOSF9 ST Rousset 8"		32-lead VFQFPN (5 x 5 mm)	Subcon Amkor

3.1 Reliability test plan and result summary

The reliability test plan and the result summary is presented in Table 4.

Table 4. Reliability test plan and result summary (32-lead VFQFPN 5 x 5 mm / Amkor)⁽¹⁾

	Test short description								
Test						Results fail / sample size			
	Method	Conditions	Sample size / lots	No. of lots	Duration	RX95HF			
						Lot 1	Lot 2	Lot 3	Lot 4 (2)
	Preconditioning: moisture sensitivity level 1								
PC	JESD22-A113 J-STD-020D	MSL1, peak temperature at 260 °C, 3 IReflow	231	1	N/A	0/231	-	-	-
ите	High temperature	storage life							
HTSL (3)	JESD22-A103	Retention bake at 150 °C	77	1	1008 hrs	0/77	-	-	-
	Temperature cycli	ing							
TC ⁽³⁾	JESD22-A104	–65 °C / +150 °C	77	1	1000 cycles	0/77	-	-	-
	Autoclave (pressu	ure pot)							
AC ⁽³⁾	JESD22-A102	121 °C, 100% RH at 2 ATM	77	1	96 hrs	0/77	-	-	-
HTOL	High temperature operating life								
(4)	JESD22-A108	HTOL 140 °C, 5V	77	3	1008 hrs	0/77	0/77	0/77	-
Electrostatic discharge (human body model)									
HBM (4)	JESD22-A114	C = 100 pF, R= 1500 Ω	27	3	N/A	Pass 2000V	Pass 2000V	Pass 2000V	Pass 2000V
ESD	Electrostatic discharge (machine model)								
MM (4)	JESD22-A115	C = 200 pF, R = 0 Ω	15	3	N/A	Pass 200V	Pass 200V	Pass 200V	Pass 200V
	Electrostatic discharge (charge device model)								
ESD CDM	JESD22-C101	Field induced charging method	12	1	N/A	Pass 1000V	-	-	-
	Latch-up (current	injection and overvoltage	stress)						
LU ⁽⁴⁾	JESD78A	At maximum operating temperature (85 °C)	6	3	N/A	Class II Level A	Class II Level A	Class II Level A	Class II Level A

1. See Table 5: List of terms for a definition of abbreviations.

2. Reliability results on lot 4 obtained on improved design (PCN MMS-MMY/14/8745).

3. HTSL-, TC-, AC- dedicated parts are first subject to preconditioning flow.

4. Performed on engineering ceramic package CDIP24.



4 Applicable and reference documents

- AEC-Q100: Stress test qualification for integrated circuits
- SOP 2.6.10: General product qualification procedure
- SOP 2.6.11: Program management fro product qualification
- SOP 2.6.12: Design criteria for product qualification
- SOP 2.6.14: Reliability requirements for product qualification
- SOP 2.6.19: Process maturity level
- SOP 2.6.2: Process qualification and transfer management
- SOP 2.6.20: New process / New product qualification
- SOP 2.6.7: Product maturity level
- SOP 2.6.9: Package and process maturity management in Back End
- SOP 2.7.5: Automotive products definition and status
- JESD22-A101: Steady state temperature humidity bias life test
- JESD22-A102: Accelerated moisture resistance unbiased autoclave
- JESD22-A103: High temperature storage life
- JESD22-A104: Temperature cycling
- JESD22-A108: Temperature, bias, and operating life
- JESD22-A113: Preconditioning of nonhermetic surface mount devices prior to reliability testing
- JESD22-A114: Electrostatic discharge (ESD) sensitivity testing human body model (HBM)
- JESD22-A115: Electrostatic discharge (ESD) sensitivity testing machine model (MM)
- JESD22-C101: Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components
- JESD78A: IC Latch-up test
- J-STD-020D: Moisture/reflow sensitivity classification for nonhermetic solid state surface mount devices



5 Glossary

Terms	Description
HTOL	High temperature operating life
ESD HBM	Electrostatic discharge (human body model)
ESD MM	Electrostatic discharge (machine model)
LU	Latch-up
PC	Preconditioning (solder simulation)
ТНВ	Temperature humidity bias
тс	Temperature cycling
AC	Autoclave (pressure pot)
HTSL	High temperature storage life
ESD CDM	Electrostatic discharge (charge device model)



6 Revision history

Date	Revision	Changes
30-Sep-2013	1	Initial release.
09-Oct-2014	2	<i>Table 4</i> updated with reliability results obtained on improved design (PCN MMS-MMY/14/8745).

Table 6. Document revision history



IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2014 STMicroelectronics – All rights reserved



RX95HF, Design improvement for die version rationalization

Document Revision History					
Date	Rev.	Description of the Revision			
October 3rd, 2014	1.00	First draft creation			

Source Documents & Reference Documents					
Source document Title	Rev.:	Date:			

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

RESTRICTIONS OF USE AND CONFIDENTIALITY OBLIGATIONS:

THIS DOCUMENT AND ITS ANNEXES CONTAIN ST PROPRIETARY AND CONFIDENTIAL INFORMATION. THE DISCLOSURE, DISTRIBUTION, PUBLICATION OF WHATSOEVER NATURE OR USE FOR ANY OTHER PURPOSE THAN PROVIDED IN THIS DOCUMENT OF ANY INFORMATION CONTAINED IN THIS DOCUMENT AND ITS ANNEXES IS SUBMITTED TO ST PRIOR EXPRESS AUTHORIZATION. ANY UNAUTHORIZED REVIEW, USE, DISCLOSURE OR DISTRIBUTION OF SUCH INFORMATION IS EXPRESSLY PROHIBITED.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2014 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com